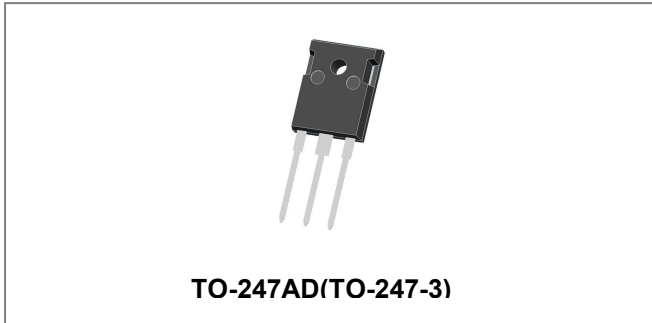


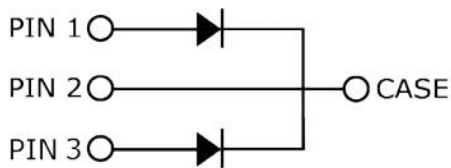
S4D30120D 1200V SiC POWER SCHOTTKY RECTIFIER



Description

S4D30120D is a single SiC Schottky rectifier packaged in TO-247AD(TO-247-3) case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D30120D is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	1200	V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F(AV)1}	T _c =25°C	46 (per leg)	A
	I _{F(AV)2}	T _c =148°C	92 (per device)	A
15 (per leg)			A	
30 (per device)				
Peak One Cycle Non-Repetitive Surge Current (per leg)	I _{FSM}	10ms, Half Sine pulse, T _c = 25 °C	130	A
Repetitive Peak Forward Surge Current (per leg)	I _{FRM}	10ms, Half Sine pulse, T _c = 25 °C	68	A
Power Dissipation (per leg)	P _{tot1}	T _c =25°C	178.6	W
	P _{tot1}	T _c =110°C	77.4	W

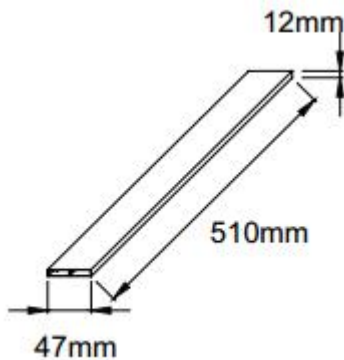
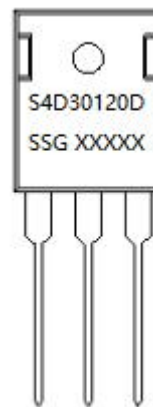
Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg)*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 15A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current (per leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	3	40	uA
	I _{R2}	@V _R = rated V _R T _J = 175 °C	10	50	uA
Junction Capacitance(per leg)	C _T	V _R =0V, T _J =25°C, f=1MHz	990	-	pF
Reverse Recovery Charge(per leg)	Q _c	I _F = 15A, di/dt = 200A/μs V _R = 800 V, T _J =25°C	76.32	-	nC
Capacitance Stored Energy(per leg)	E _c	V _R = 800 V, T _J =25°C	39.24	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation, T _J =25°C	0.84(per leg) 0.42(both leg)	°C/W

Tube Specification

Marking Diagram


Where XXXXX is YYWWL

S4D = Device Type
D = Package type
30 = Forward Current (30A)
120 = Reverse Voltage (1200V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
S4D30120D	TO-247AD(TO-247-3)	25pcs /tube

Ratings and Characteristics Curves (per leg)

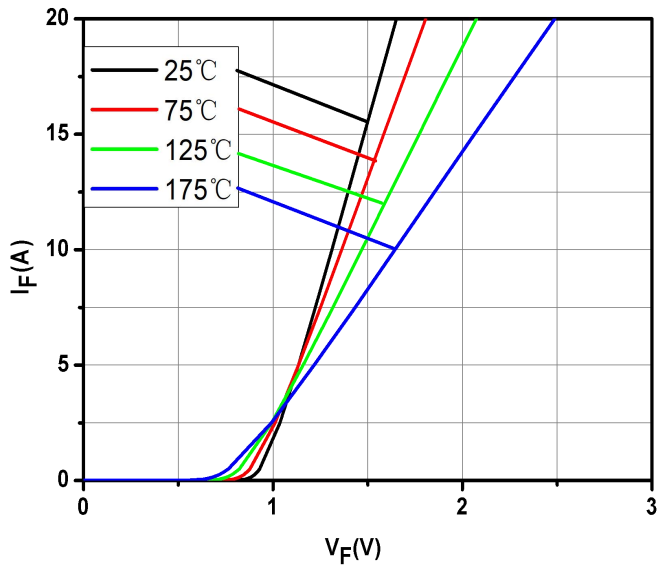


Fig.1-Typical Forward Voltage Characteristics

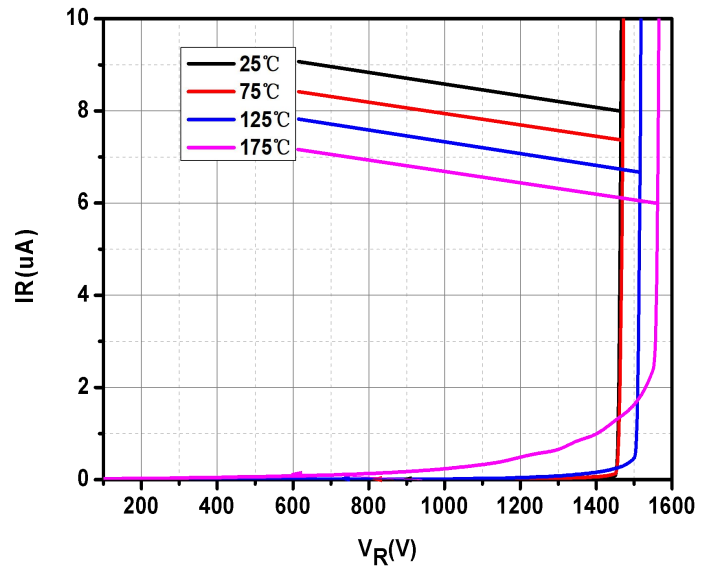


Fig.2-Typical Reverse Characteristics

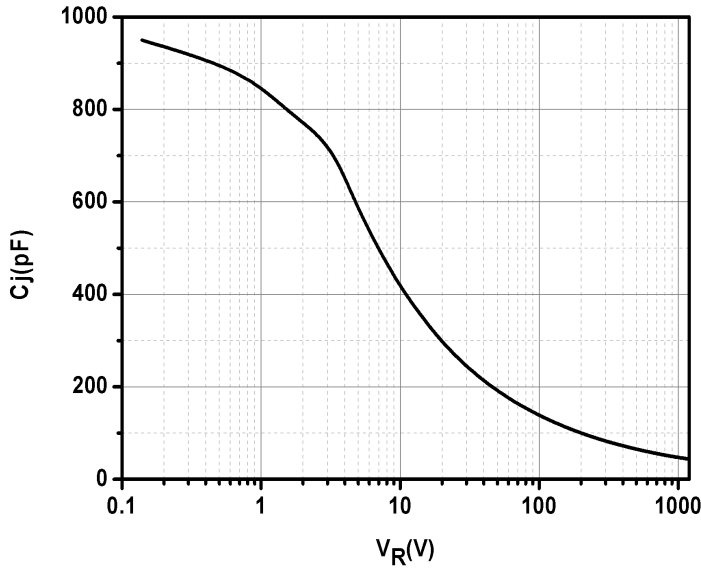


Fig.3-Capacitance vs. Reverse Voltage

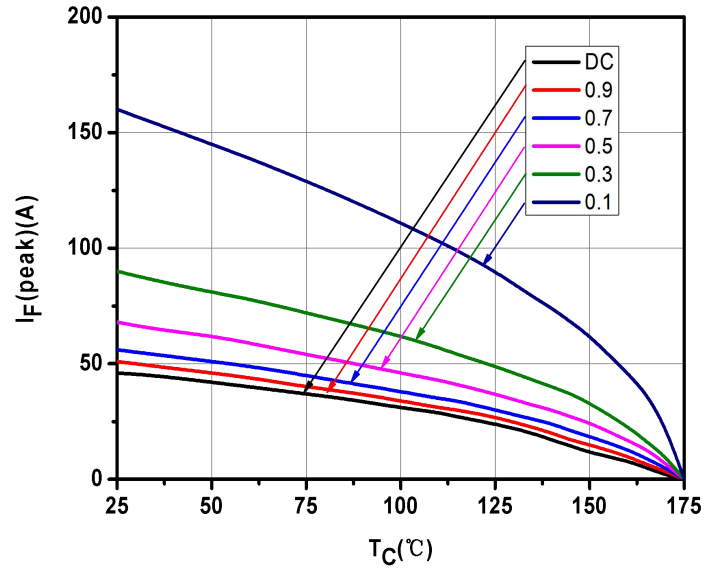


Fig.4-Current Derating

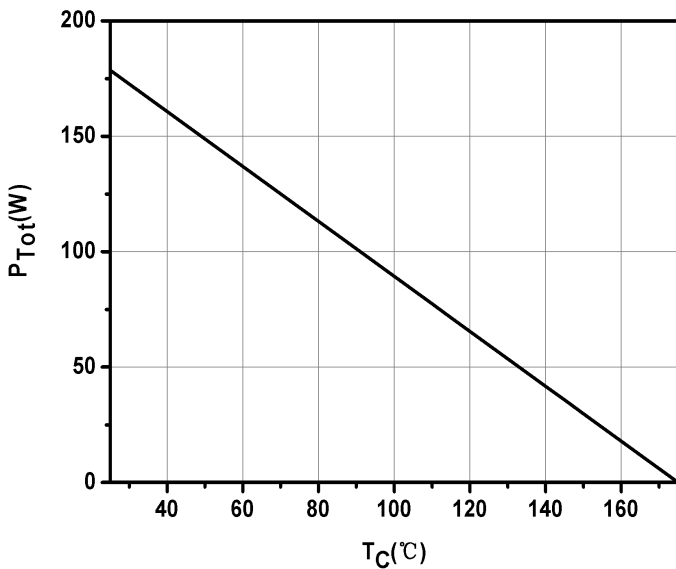


Fig.5-Power Derating

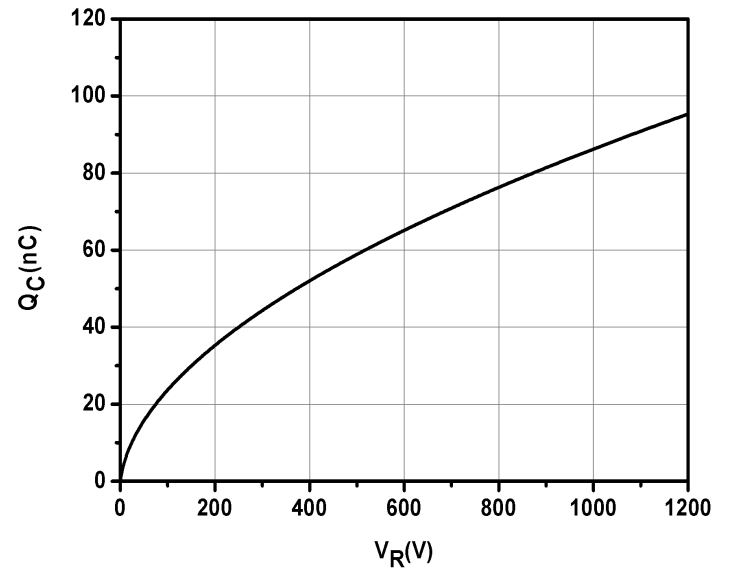


Fig.6-Total Capacitance Charge vs. Reverse Voltage

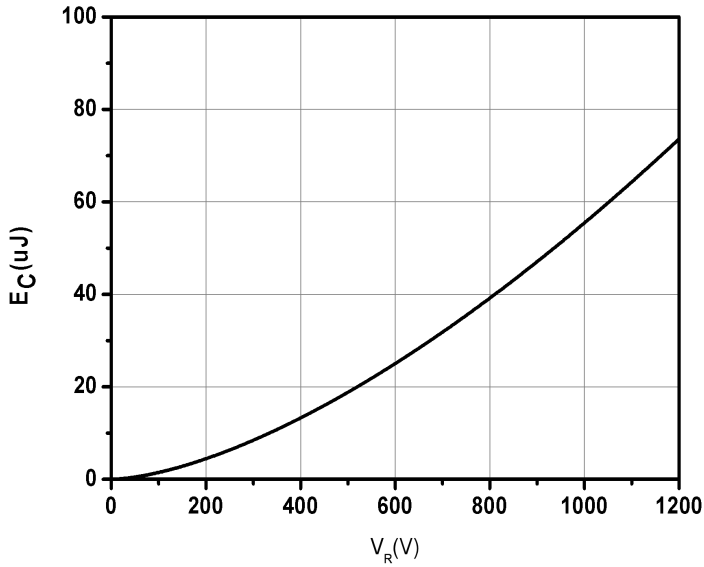
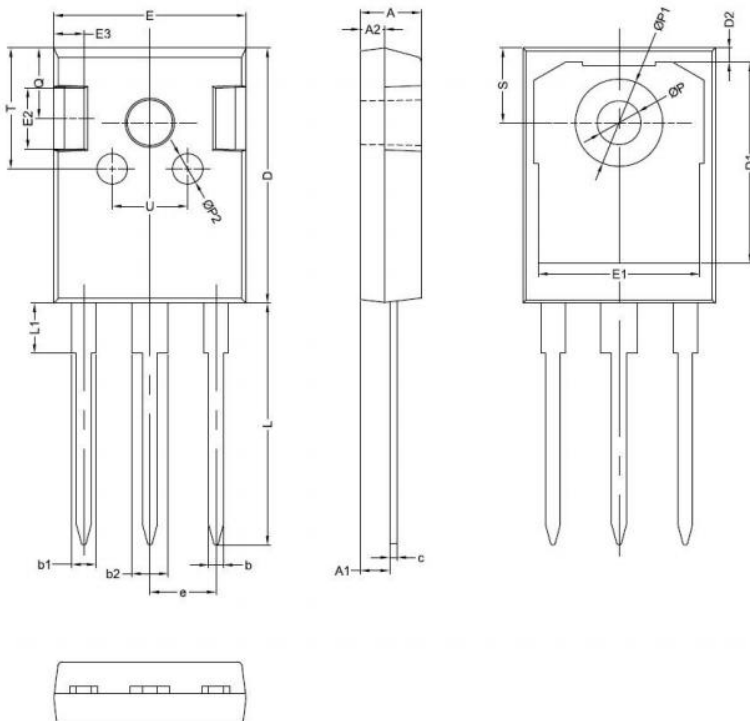


Fig.7-Capacitance Stored Energy

Mechanical Dimensions TO-247AD



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

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